



STD60NH03L STD60NH03L-1

N-channel 30V - 0.0075Ω - 60A - DPAK/IPAK
STripFET™ III Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STD60NH03L-1	30V	<0.009Ω	60A
STD60NH03L	30V	<0.009Ω	60A

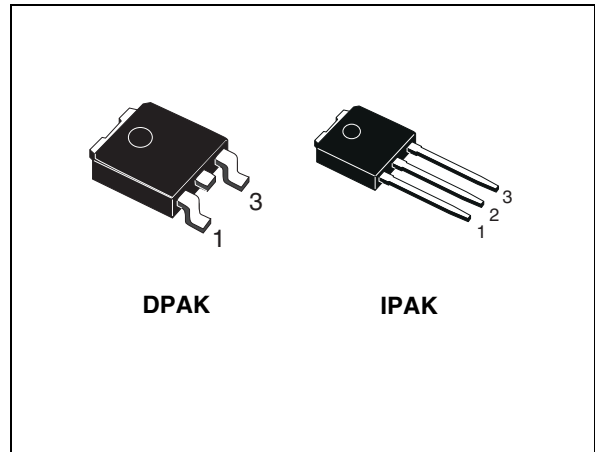
- R_{DS(ON)} x Q_g industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low threshold device

Description

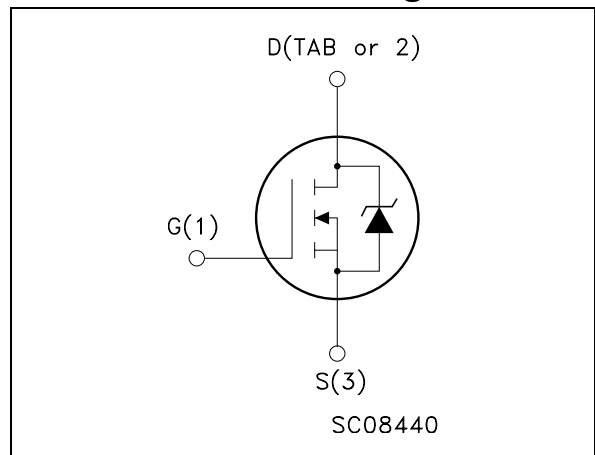
The device utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for the most demanding DC-DC converter application where high efficiency is to be achieved, of paramount importance.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STD60NH03LT4	D60NH03L	DPAK	Tape & reel
STD60NH03L-1	D60NH03L	IPAK	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	30	V
V_{GS}	Gate- source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	60	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	43	A
$I_{DM}^{(1)}$	Drain current (pulsed)	240	A
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	300	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Pulse width limited by safe operating area.

2. Starting $T_j=25^\circ\text{C}$, $I_D=30\text{A}$, $V_{DD}=20\text{V}$

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case max	2.14	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-to ambient max	100	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-to pcb max	43	$^\circ\text{C/W}$
T_J	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

1. When mounted on minimum foot-print

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 30\text{A}$ $V_{GS} = 5\text{V}$, $I_D = 30\text{A}$		0.0075 0.009	0.009 0.017	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 18\text{A}$		25		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$		2200 380 49		pF pF pF
R_G	Gate input resistance	$f=1\text{ MHz}$ Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.5		Ω
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 15\text{V}$, $I_D = 30\text{A}$ $R_G = 4.7\Omega$, $V_{GS} = 5\text{V}$ (see Figure 13)		21 95 19 15		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 15\text{V}$, $I_D = 60\text{A}$, $V_{GS} = 5\text{V}$, $R_G = 4.7\Omega$ (see Figure 14)		15.7 8.3 3.4	21	nC nC nC
$Q_{gls}^{(2)}$	Third-quadrant gate charge	$V_{DS} < 0\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$		15		nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. Gate charge for synchronous operation. See [Chapter 4: Appendix A](#)

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				60 240	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 30A$, $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 60A$, $di/dt = 100A/\mu s$, $V_{DD} = 20V$, $T_j = 150^\circ C$ (see Figure 15)		32 51 3.2		ns nC A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

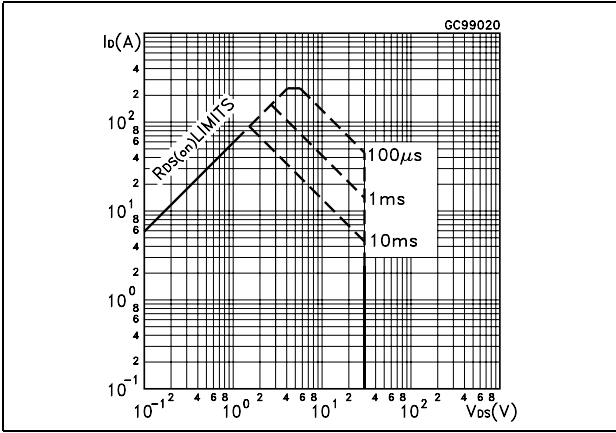


Figure 2. Thermal impedance

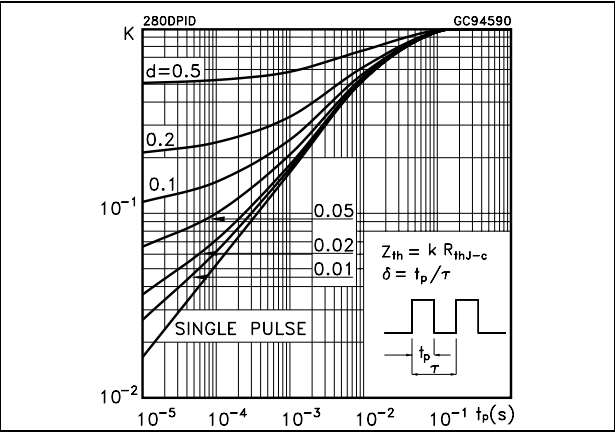


Figure 3. Output characteristics

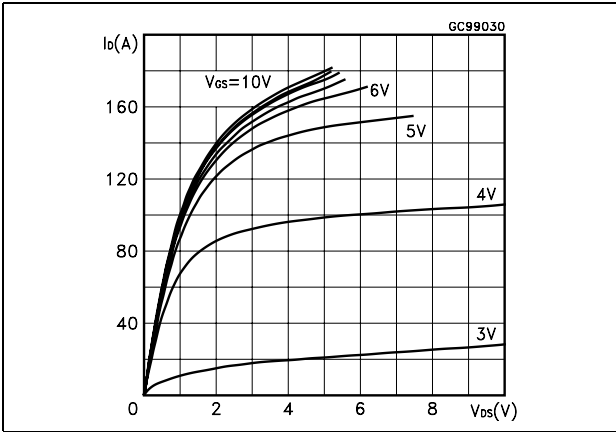


Figure 4. Transfer characteristics

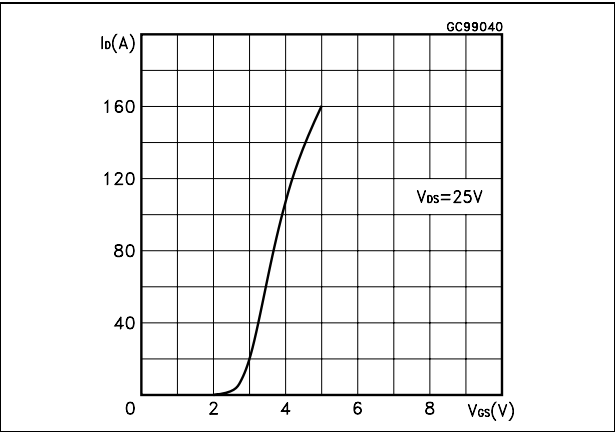


Figure 5. Transconductance

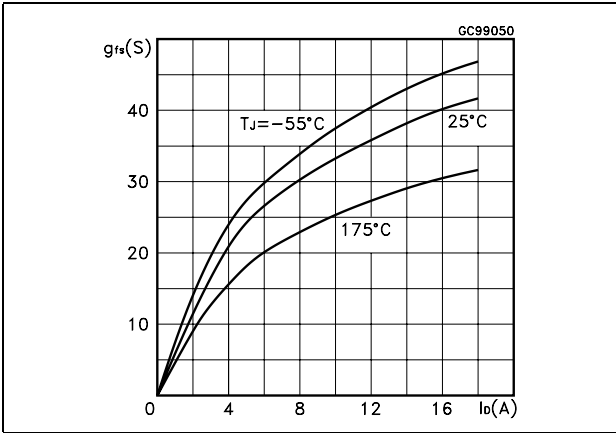


Figure 6. Static drain-source on resistance

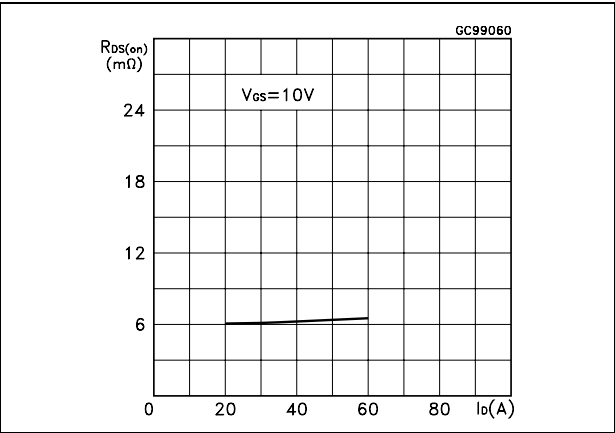


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

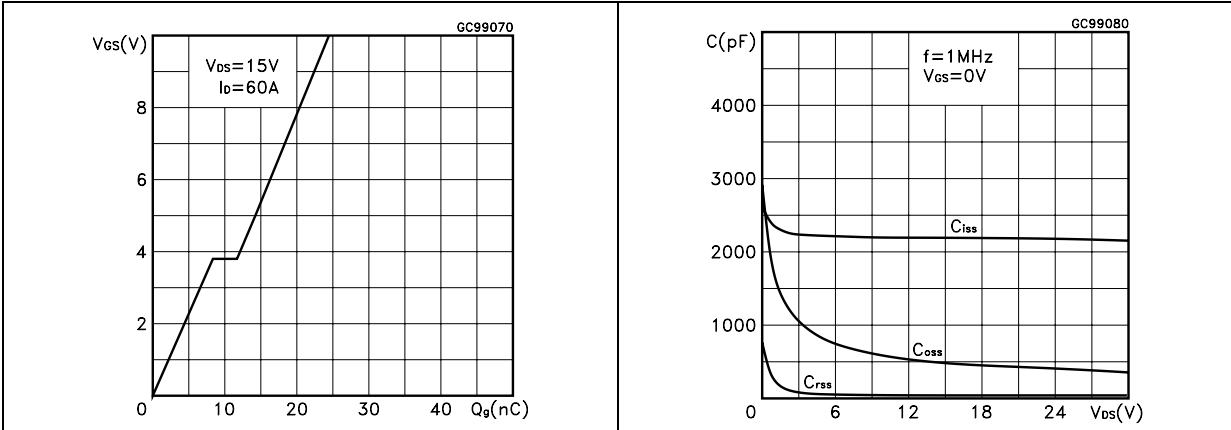


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

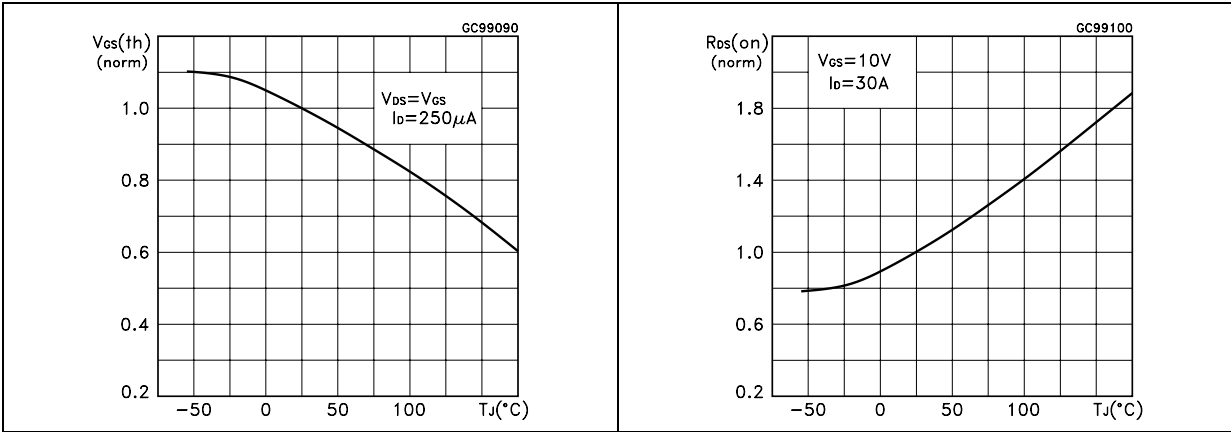
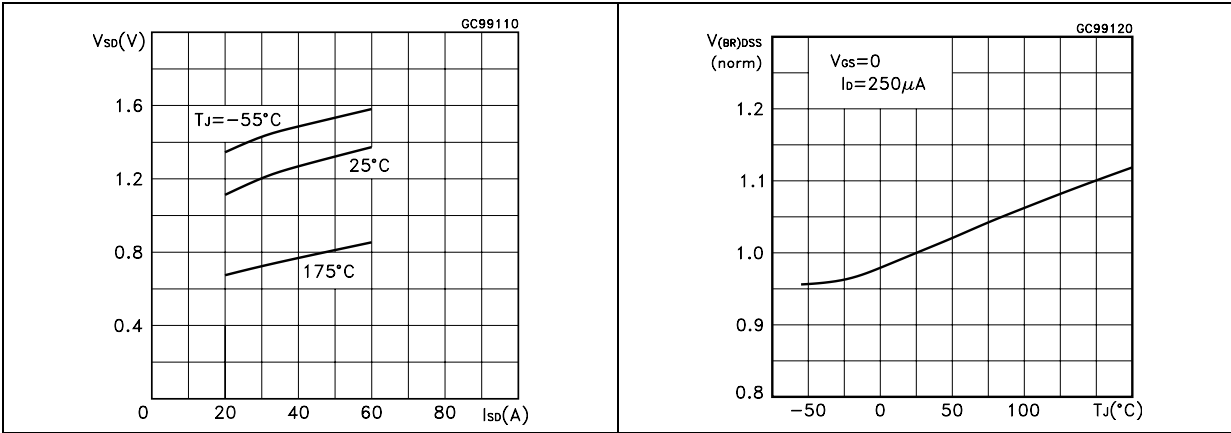


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized breakdown voltage vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

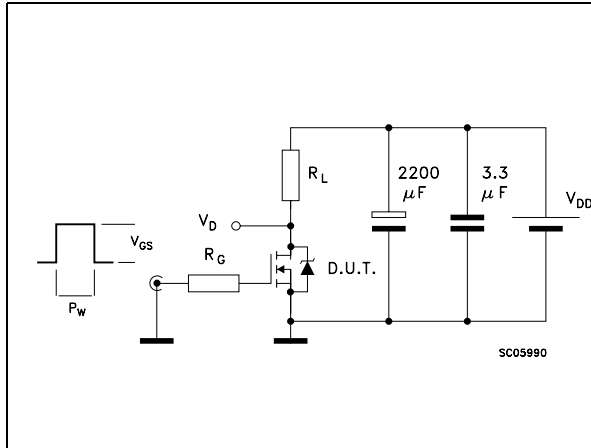


Figure 14. Gate charge test circuit

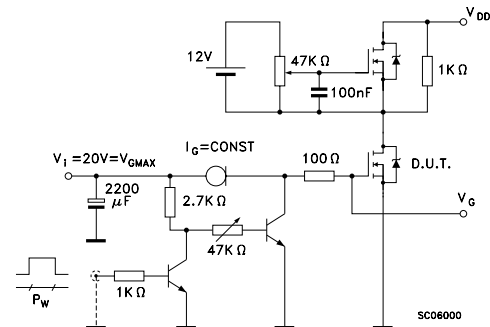


Figure 15. Test circuit for inductive load switching and diode recovery times



Figure 16. Unclamped Inductive load test circuit

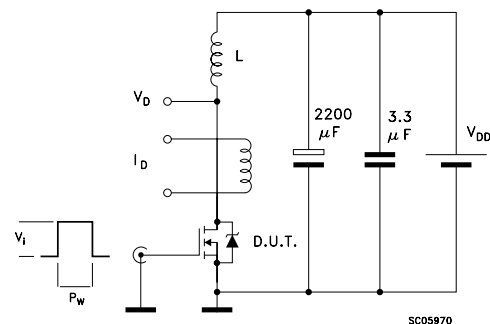


Figure 17. Unclamped inductive waveform

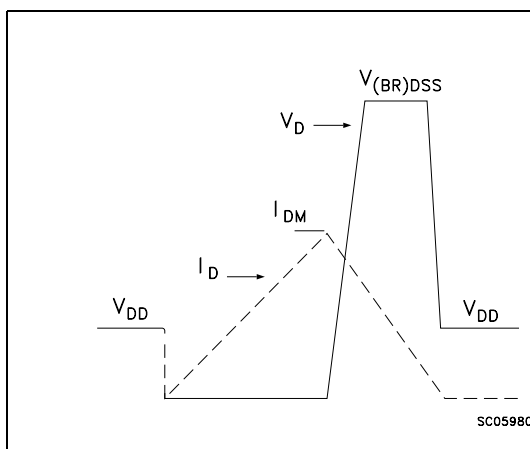
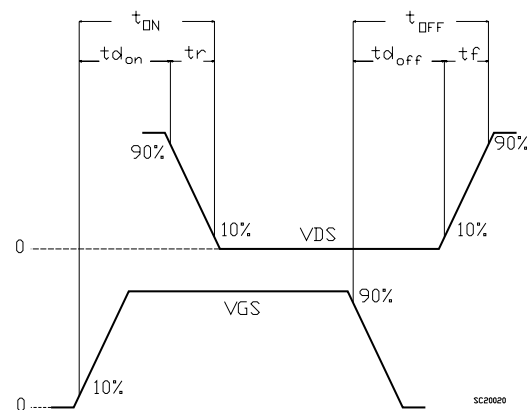
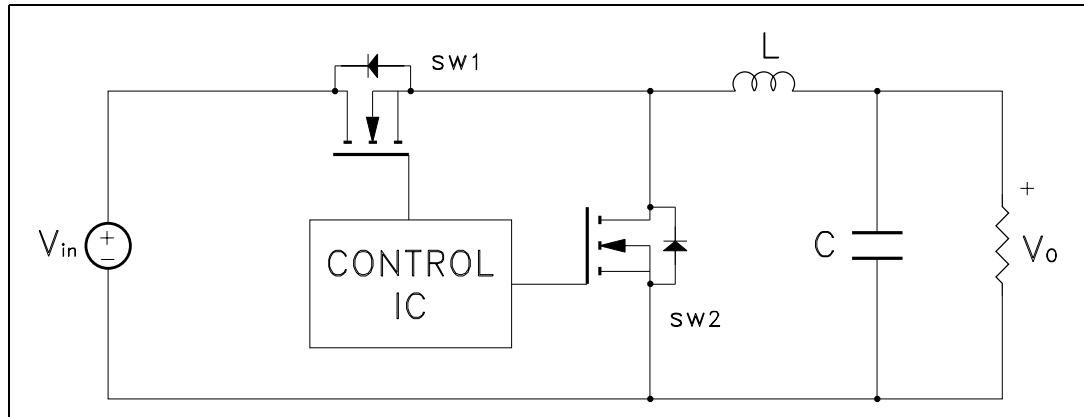


Figure 18. Switching time waveform



4 Appendix A

Figure 19. Buck converter: power losses estimation



The power losses associated with the FETs in a synchronous buck converter can be estimated using the equations shown in the table below. The formulas give a good approximation, for the sake of performance comparison, of how different pairs of devices affect the converter efficiency. However a very important parameter, the working temperature, is not considered. The real device behavior is really dependent on how the heat generated inside the devices is removed to allow for a safer working junction temperature.

- The low side (SW2) device requires:
- Very low $R_{DS(on)}$ to reduce conduction losses
- Small Q_{gs} to reduce the gate charge losses
- Small C_{oss} to reduce losses due to output capacitance
- Small Q_{rr} to reduce losses on SW1 during its turn-on
- The C_{gd}/C_{gs} ratio lower than V_{th}/V_{gg} ratio especially with low drain to source voltage to avoid the cross conduction phenomenon;
- The high side (SW1) device requires:
- Small R_g and L_s to allow higher gate current peak and to limit the voltage feedback on the gate
- Small Q_g to have a faster commutation and to reduce gate charge losses
- Low $R_{DS(on)}$ to reduce the conduction losses.

Table 6. Power losses calculation

	High side switching (SW1)	Low side switch (SW2)
Pconduction	$R_{DS(on)SW1} * I_L^2 * \delta$	$R_{DS(on)SW2} * I_L^2 * (1 - \delta)$
Pswitching	$V_{in} * (Q_{gsth(SW1)} + Q_{gd(SW1)}) * f * \frac{I_L}{I_g}$	Zero Voltage Switching

Table 6. Power losses calculation

		High side switching (SW1)	Low side switch (SW2)
P _{diode}	Recovery ⁽¹⁾	Not applicable	$V_{in} * Q_{rr(SW2)} * f$
	Conduction	Not applicable	$V_{f(SW2)} * I_L * t_{deadtime} * f$
P _{gate} (Q _G)		$Q_{g(SW1)} * V_{gg} * f$	$Q_{gls(SW2)} * V_{gg} * f$
P _{Qoss}		$\frac{V_{in} * Q_{oss(SW1)} * f}{2}$	$\frac{V_{in} * Q_{oss(SW2)} * f}{2}$

1. Dissipated by SW1 during turn-on

Table 7. Paramiters meaning

Parameter	Meaning
d	Duty-cycle
Q _{gsth}	Post threshold gate charge
Q _{gls}	Third quadrant gate charge
P _{conduction}	On state losses
P _{switching}	On-off transition losses
P _{diode}	Conduction and reverse recovery diode losses
P _{gate}	Gate drive losses
P _{Qoss}	Output capacitance losses

5 Package mechanical data

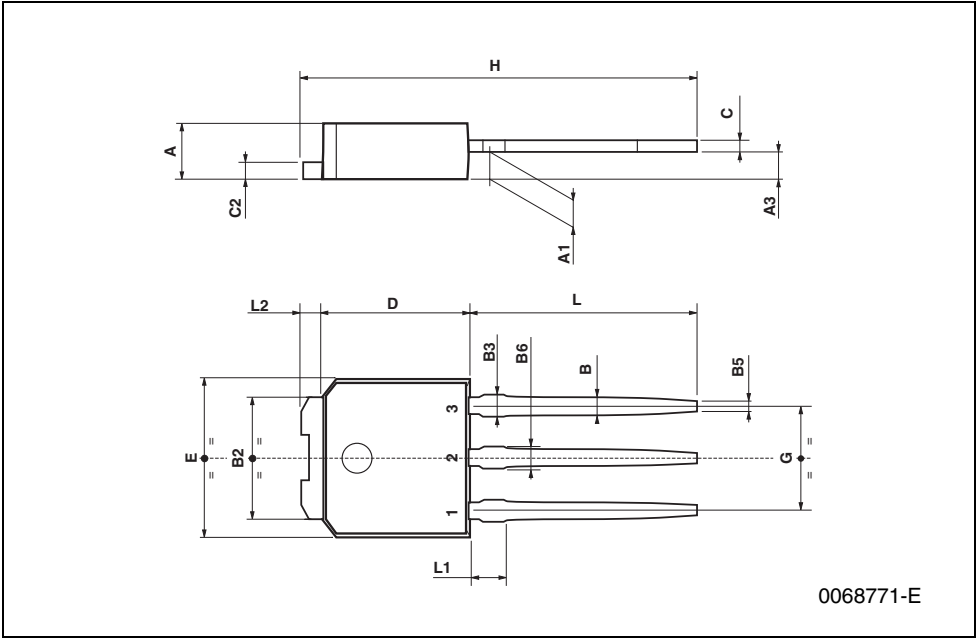
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

DPAK MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

The mechanical drawing illustrates the STD60NH03L package in three views: top, side, and a detailed cross-section. The top view shows dimensions E (total width), b4 (lead width), and e (lead pitch). The side view shows dimensions A (height), A1 (lead height), A2 (lead thickness), B (lead width), C (lead thickness), C2 (lead thickness), D (total height), D1 (lead height), E1 (lead width), e1 (lead pitch), H (total height), L (lead length), L1 (lead length), L2 (lead length), L4 (lead length), R (lead radius), and V2 (lead angle). The detailed cross-section shows the SEATING PLANE, GAUGE PLANE, and THERMAL PAD. The drawing is labeled 0068772-F.

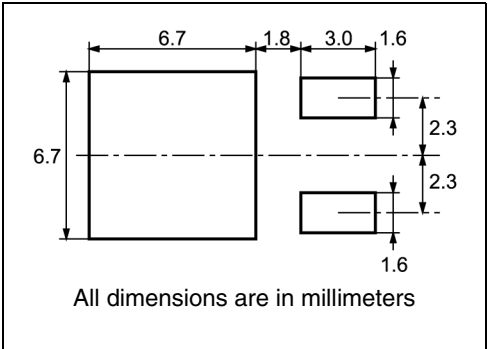
TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

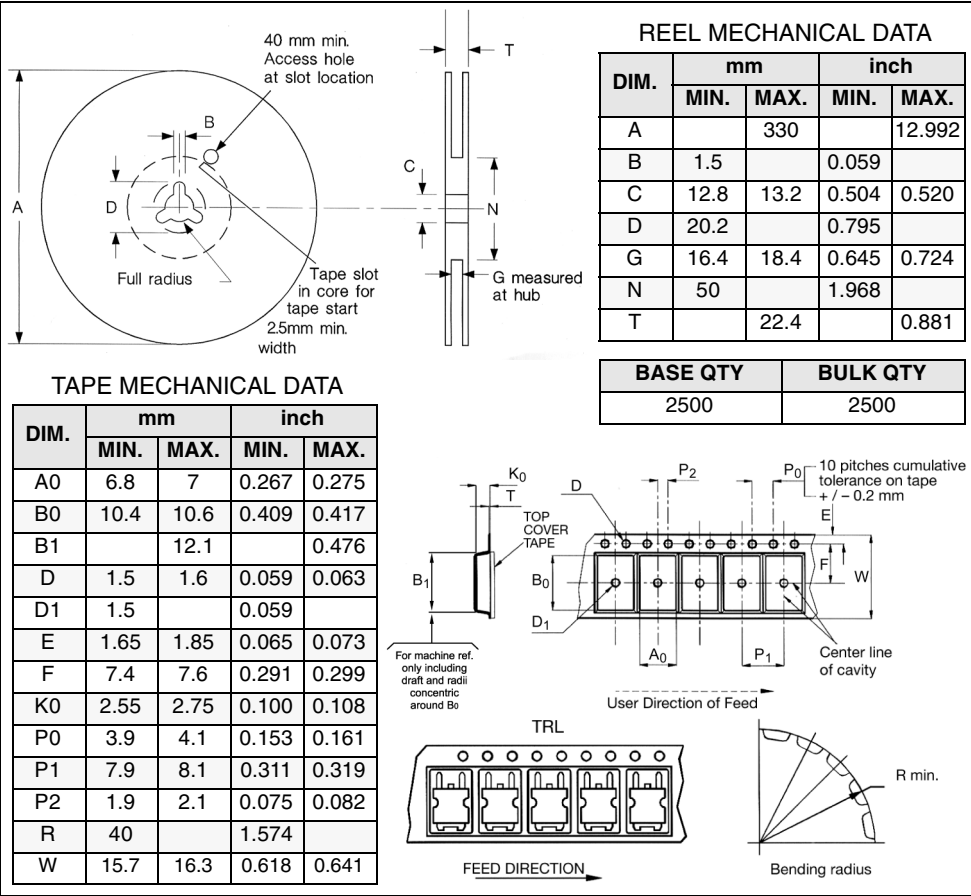


6 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



7 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	5	Preliminary version
19-Jul-2006	6	New template, no content change

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